

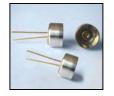
ROITHNER LASERTECHNIK GIRDH

WIEDNER HAUPTSTRASSE 76 IO40 VIENNA AUSTRIA TEL. +43 I 586 52 43 -0, FAX. -44, OFFICE@ROITHNER-LASER.COM



LED20FC-PR-WIN

TECHNICAL DATA



Mid-Infrared Light Emitting Diode, Flip-Chip Design

Light Emitting Diodes with central wavelength 2.02 µm series are based on heterostructures grown on GaSb substrates by LPE. Solid solutions AlGaAsSb are used in the active layer. Wide band gap solid solutions AlGaAsSb with Al content 64% are used for good electron confinement. LED20FC-PR-WIN has a stable ouput power and a lifetime more then 80000 hours.

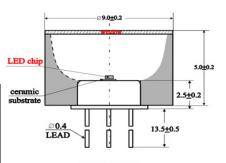
Features

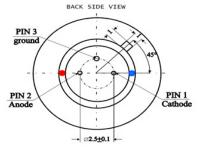
- Structure: GalnAsSb/AlGaAsSb, Flip-Chip Design
- Peak Wavelength: typ. 2.02 μm
- Optical Ouput Power: typ. 1.2 mW qCW
- Package: TO-18, with PR and window



Specifications

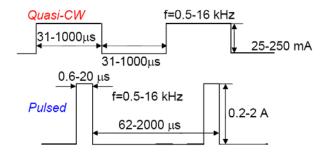
Item	Condition	Min.	Rating Typ.	Max.	Unit
Peak Wavelength	T=300 K	2.00	2.02	2.09	μm
FWHM	150 mA CW	100	150	250	nm
Quasi-CW Optical Power	200 mA qCW	0.8	1.2	1.8	mW
Pulsed Optical Power	1 A	20	30	40	mW
Switching Time	T=300 K	10	20	30	ns
Operation Voltage	200 mA qCW				V
Operating Temperature	-240 + 50				°C
Emitting Area	670x770				μm
Soldering Temperature	180				ů
Package	TO-18, with parabolic reflector and quartz window				•





(Unit: mm)

Operating Regime



Quasi-CW

- Maximum current 220 mA
- Recommended current 150-200mA

Pulsed

 Maximum current 1 A (puls lenght 500 ns, repetition rate 2kHz)



ROITHNER LASERTECHNIK GIRDH

WIEDNER HAUPTSTRASSE 76

1040 VIENNA **AUSTRIA** TEL. +43 I 586 52 43 -0, FAX. -44, OFFICE@ROITHNER-LASER.COM



Typical Performance Curves

